

Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)



Complete if Known

Application Number	10/623788
Filing Date	July 21, 2003
First Named Inventor	Forbes, Leonard
Group Art Unit	2811
Examiner Name	Unknown

Sheet 1 of 7

Attorney Docket No: 1303.109US1

US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
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Substitute Disclosure Statement Form (PTO-1449)

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached

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Leonard Forbes

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3/18/06

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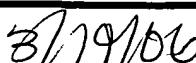
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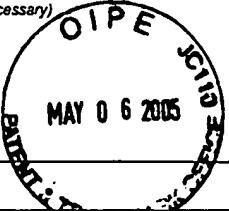
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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>		<small>Complete if Known</small> <table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td style="width: 50%;">Application Number</td> <td>10/623,788</td> </tr> <tr> <td>Filing Date</td> <td>July 21, 2003</td> </tr> <tr> <td>First Named Inventor</td> <td>Forbes, Leonard</td> </tr> <tr> <td>Group Art Unit</td> <td>2811</td> </tr> <tr> <td>Examiner Name</td> <td>Unknown</td> </tr> </table>		Application Number	10/623,788	Filing Date	July 21, 2003	First Named Inventor	Forbes, Leonard	Group Art Unit	2811	Examiner Name	Unknown
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		Attorney Docket No: 1303.109US1											
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		Application Number	10/623,788
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		Group Art Unit	2811
		Examiner Name	Unknown
Sheet 2 of 2		Attorney Docket No: 1303.109US1	

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		Application Number	10/623,788
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		First Named Inventor	Forbes, Leonard
		Group Art Unit	2822
		Examiner Name	Perkins, Pamela
Sheet 1 of 1		Attorney Docket No: 1303.109US1	

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